. reescale Semiconductor Technical Data

Document Number: MHW9146N

Rev. 4, 5/2006

Gallium Arsenide CATV Amplifier Module

Features

- Specified for 79-, 112- and 132-Channel Loading
- **Excellent Distortion Performance**
- Built-in Input Diode Protection
- GaAs FET Transistor Technology
- Unconditionally Stable Under All Load Conditions

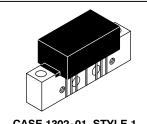
Applications

- CATV Systems Operating in the 40 to 870 MHz Frequency Range
- Input Stage Amplifier in Optical Nodes, Line Extenders and Trunk Distribution Amplifiers for CATV Systems
- Output Stage Amplifier on Applications Requiring Low Power Dissipation and High Output Performance
- Driver Amplifier in Linear General Purpose Applications

- 24 Vdc Supply, 40 to 870 MHz, CATV GaAs Forward Amplifier Module
- Replaced MHW9146. There are no form, fit or function changes with this part replacement.
- **RoHS Compliant**

MHW9146N

870 MHz **14.3 dB GAIN** 132-CHANNEL **GaAs CATV AMPLIFIER MODULE**



CASE 1302-01, STYLE 1

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
RF Voltage Input (Single Tone)	V _{in}	+65	dBmV
DC Supply Voltage	V _{CC}	+26	Vdc
Operating Case Temperature Range	T _C	-20 to +100	°C
Storage Temperature Range	T _{stg}	-40 to +100	°C

Table 2. ESD Maximum Ratings

Rating	Input Value	Output Value	Unit
Surge Voltage per IEC 1000-4-5	200	200	V
Human Body Model per Mil. Std. 1686	2	2	kV

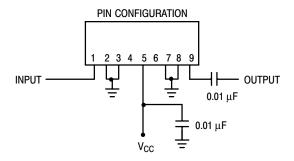
Table 3. Electrical Characteristics ($V_{CC} = 24 \text{ Vdc}$, $T_{C} = +45^{\circ}\text{C}$, 75 Ω system unless otherwise noted)

Cr	naracteristic	Symbol	Min	Тур	Max	Unit
Frequency Range		BW	40	_	870	MHz
Power Gain	870 MHz	G _p	13.8	14.3	14.8	dB
Slope	40-870 MHz	S	0	0.4	1.0	dB
Gain Flatness (40-870 MHz, Pe	Gain Flatness (40-870 MHz, Peak-to-Valley)		_	_	0.5	dB
Return Loss — Input (Z ₀ = 75 Ohms)	40-500 MHz f > 501 MHz	IRL	20 18	_ _		dB
Return Loss — Output (Z ₀ = 75 Ohms)	40-160 MHz f > 160 MHz	ORL	20 18			dB



Table 3. Electrical Characteristics (V_{CC} = 24 Vdc, T_C = +45°C, 75 Ω system unless otherwise noted) (continued)

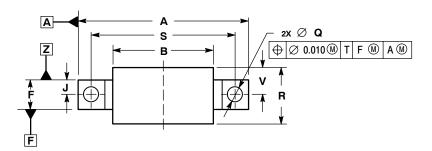
Characteristic		Symbol	Min	Тур	Max	ı
Composite Second Order						
(V _{out} = +48 dBmV/ch., Worst Case)	79-Channel FLAT	CSO ₇₉		-68	-64	
(V _{out} = +46 dBmV/ch., Worst Case)	112-Channel FLAT	CSO ₁₁₂		-63	-60	
(V _{out} = +44 dBmV/ch., Worst Case)	132-Channel FLAT	CSO ₁₃₂	_	-63	-60	
Cross Modulation Distortion @ Ch 2						
$(V_{out} = +48 \text{ dBmV/ch.}, FM = 55.25 \text{ MHz})$	79-Channel FLAT	XMD ₇₉		-60	-55	
(V _{out} = +46 dBmV/ch., FM = 55.25 MHz)	112-Channel FLAT	XMD ₁₁₂		-60	-55	
$(V_{out} = +44 \text{ dBmV/ch.}, FM = 55.25 \text{ MHz})$	132-Channel FLAT	XMD ₁₃₂	_	-60	-55	
Composite Triple Beat						
(V _{out} = +48 dBmV/ch., Worst Case)	79-Channel FLAT	CTB ₇₉		-64	-60	
(V _{out} = +46 dBmV/ch., Worst Case)	112-Channel FLAT	CTB ₁₁₂		-64	-60	
(V _{out} = +44 dBmV/ch., Worst Case)	132-Channel FLAT	CTB ₁₃₂	_	-64	-60	
Noise Figure	50 MHz	NF	_	4.4	5.5	
	550 MHz			3.8	_	
	750 MHz		_	4.0	_	
	870 MHz		_	4.3	5.5	
DC Current (V _{DC} = 24 V, T _C = 45°C)		I _{DC}	230	245	260	
Note: This device requires an external 0.01 μF	DC blocking capacitor conn PIN CONFIGURA		put pin (Pin	9) as indicate	ed in Figure	1.
Note: This device requires an external 0.01 μF	PIN CONFIGURA	7 8 9	out pin (Pin	9) as indicate	ed in Figure	1.

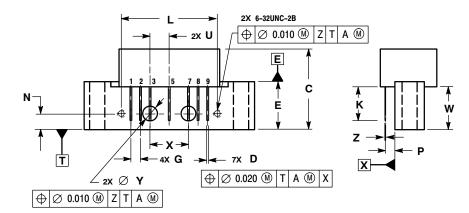




ARCHIVE INFORMATION

PACKAGE DIMENSIONS





- NOTES:
 1. DIMENSIONS ARE IN INCHES.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α		1.775		45.085
В		1.085		27.559
С		0.840		21.336
D	0.015	0.021	0.381	0.533
Е	0.465	0.510	11.811	12.954
F	0.300	0.325	7.62	8.255
G	0.100	BSC	2.540	BSC
J	0.156	BSC	3.962	BSC
K	0.315	0.355	8.001	9.017
L	1.000	BSC	25.400 BSC	
N	0.165	BSC	4.191 BSC	
Р	0.100	BSC	2.540	BSC
Q	0.148	0.168	3.759	4.267
R		0.600		15.24
S	1.500	1.500 BSC		0 BSC
U	0.200	BSC	5.080	BSC
٧		0.250		6.350
W	0.435		11.049	
Х	0.400	0.400 BSC		0 BSC
Y	0.152	0.163	3.861	4.140
Z	0.009	0.011	0.229	0.279

- STYLE 1:
 PIN 1. RF INPUT
 2. GROUND
 3. GROUND
 4. DELETED
 5. VDC
 6. DELETED
 7. GROUND
 8. GROUND
 9. RF OUTPUT

CASE 1302-01 ISSUE E



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